

Self-doping instability of the Wigner-Mott insulator

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We present a theory describing the mechanism for the two-dimensional (2D) metal-insulator transition (MIT) in the absence of disorder. A two-band Hubbard model is introduced, describing vacancy-interstitial pair excitations within the Wigner crystal. Kinetic energy gained by delocalizing such excitations is found to lead to an instability of the insulator to self-doping above a critical carrier concentration $n=n_c$, mapping the problem to a density-driven Mott MIT. This mechanism provides a natural explanation of several puzzling experimental features, including the large effective mass enhancement, the large resistivity drop, and the large positive magnetoresistance on the metallic side of the transition. We also present a global phase diagram for the clean 2D electron gas as a function of n and parallel magnetic field B_{\parallel} , which agrees well with experimental findings in ultraclean samples.

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INTRODUCTION

Significant experimental advances¹ over the past ten years have provided beautiful and convincing evidence for the existence of a sharp metal-insulator transition (MIT) in two-dimensional (2D) electron gases (2DEG). This progress has sparked much renewed interest in better understanding the basic physical mechanisms that drive the MIT, a fundamental physical question that has remained poorly understood for many years.

One important issue relates to the stability of an interacting 2D metal with respect to disorder. While even weak disorder is known to destroy any 2D metal in the absence of interactions,² very recent work³ has provided strong theoretical evidence that electron-electron interactions may stabilize a 2D metallic phase. This theory focuses on the most singular hydrodynamic corrections within the low temperature diffusive regime, and views disorder as the principal driving force that produces the insulating state.

It should be emphasized, though, that the best evidence for a sharp MIT is found in the cleanest samples, where the diffusive regime is restricted to low densities and extremely low temperatures. Indeed, the experimental data¹ demonstrating strong effective mass m^* enhancements have all been obtained in the ballistic regime, where diffusive processes are irrelevant. An important question then arises: How many of the key experimental features can be understood by deliberately disregarding disorder, and focusing on interaction effects alone as the main driving force for the transition? This question is the main subject of this paper, where we propose the quantum melting of a Wigner crystal as the fundamental mechanism for the MIT in a sufficiently clean 2DEG.

It is well known that at the lowest carrier densities the 2D electrons form a triangular Wigner lattice. Here, each lattice site is occupied by a single spin 1/2 electron, since strong on-site Coulomb repulsion prevents double occupation. The Wigner crystal can therefore be viewed as a (magnetic) Mott insulator, characterized by an abundance of low-lying spin excitations, but with an appreciable energy gap to charge excitations. As density increases, the gap to vacancy-

interstitial pair formation decreases until the system undergoes a transition to a metallic state. The MIT from such a Mott insulator to a metal must, therefore, be fundamentally different from any Anderson-like transition, because the very physical nature of each insulating state is also completely different. If this idea is indeed correct—that the Wigner crystal melting is akin to a Mott MIT—then one may expect the critical behavior of the 2DEG to resemble that of other Mott systems. The canonical example for the Mott transition in a continuum system is the Fermi liquid to solid transition in normal He³. Here, very recent experiments⁴ on 2D monolayers have provided spectacular support for the Mott transition scenario. The effective mass m^* was found⁴ to be strongly enhanced, while the g factor remained essentially unrenormalized in the critical region—a behavior shockingly similar to that found in the most recent experiments¹ on the 2DEG.

These arguments provide strong motivation to approach the Wigner crystal melting as a Mott MIT, and develop an appropriate theory for the 2DEG. In the following, we describe the results of such an approach, demonstrating that the most striking experimental features of the 2D-MIT can all be simply understood within this framework.

CHARGE-TRANSFER MODEL

Our simplified description of a Wigner crystal is based on the idea that there exists a pronounced short range order in charge sector both on the metallic and insulating sides of the MIT. This idea is strongly supported by quantum Monte Carlo work,⁵ which shows that short range charge ordering changes little across the transition. It strongly suggests that, in a ballistic regime, a treatment in terms of an effective lattice model should be applicable on both sides of the transition. The most important elementary excitations across the charge gap of a Wigner crystal correspond to vacancy-interstitial pair formation.⁶ It should also be mentioned from the outset that our simplified description does not treat collective modes explicitly, their effect being accounted only through renormalization of effective microscopic parameters of the lattice.

Sufficiently deep within the insulating phase, the electrons are tightly bound to lattice sites, and such excitations can be well described by an effective charge-transfer (e.g., two-band Hubbard) model⁷ of the form

$$H = \sum_{i\sigma} \varepsilon_f f_{i\sigma}^\dagger f_{i\sigma} + \varepsilon_c c_{i\sigma}^\dagger c_{i\sigma} - \sum_{ij\sigma} t_{ij} c_{i\sigma}^\dagger c_{j\sigma} + \sum_{i\sigma} V (f_{i\sigma}^\dagger c_{i\sigma} + c_{i\sigma}^\dagger f_{i\sigma}) + \sum_i U f_{i\uparrow}^\dagger f_{i\downarrow}^\dagger f_{i\downarrow} f_{i\uparrow}. \quad (1)$$

Here, f^\dagger , f and c^\dagger , c are creation and annihilation operators for site and interstitial electrons, respectively, and U is the on-site repulsion preventing double occupation of lattice sites. In the tight-binding limit, the band structure parameters t and V , and that of the charge-transfer gap $\Delta_{ct} = \varepsilon_c - \varepsilon_f$, can be estimated by computing the appropriate wave function overlaps, leading to exponentially increasing bandwidth with density. The details of such band structure calculations will not affect any of our qualitative conclusions, and will not be reported here.

The potentially most serious limitation of our lattice model is its phenomenological treatment (see below) of elastic deformation (e.g., collective charge excitations) of the Wigner lattice. These are expected to, at the least, effectively renormalize⁶ the band structure parameters, which should be quantitatively important for the physics of self-doping which we explore. More importantly, one may question the very justification of using an effective lattice model, especially on the metallic side of the transition. There is no particular reason, however, why the suppression of charge ordering associated with lattice formation must coincide with the closing of the Mott gap and the MIT. In the absence of perfect nesting, the two transitions can occur separately, and the closing of the Mott gap may be expected to lead to an itinerant charge-ordered state. At any rate, the existence of short range order on the metallic side justifies, to a significant degree, the use of a lattice model in the inelastic regime.

MOTT TRANSITION VIA SELF-DOPING

In the Wigner-Mott insulator, the ground state the electron occupation is naturally one electron *per unit cell*. However, the lattice parameters in the 2DEG are self-consistently determined so that, as the density increases, it may become energetically favorable for the lattice spacing to slightly expand or contract, while keeping the charge density *per unit area* fixed (due to charge neutrality). If this happens, the resulting occupation per unit cell becomes $1 - \delta$, corresponding to an effective self-doping of our Wigner-Mott insulator. Similar phenomena are believed to occur near the Mott transition in He³,⁸ and in the proposed formation of the He⁴ supersolid state.⁹ Self-doping may change the precise nature of the MIT, and thus it needs to be carefully examined by properly incorporating the electrostatic considerations that are specific to a charged system of particles.

Fermi-liquid condensation energy. Self-doping can be energetically favorable, since it leads to a kinetic energy gain of delocalized carriers which condense into a Fermi liquid. The price to pay is the cost of electrostatic energy to promote a

carrier (electron or hole) across the charge-transfer gap. To assess the stability of the insulator to self-doping, one must calculate the doping dependence of the condensation energy of the incipient Fermi-liquid state. This requires solving the appropriate Hubbard model—a general problem where no reliable or accepted theoretical approach is available at present.

For our purposes, a reliable treatment may be possible, and we seek inspiration from the closely related problem of He³ monolayers.⁴ Here, the observed behavior can be *quantitatively* understood⁴ by the simplest Brinkmann-Rice (BR) theory¹¹ of the Mott transition. This indicates that one approaches an insulator with localized magnetic moments (hence a large m^* as in any heavy fermion compound), where the intersite spin correlations (measured by g^*) in the Mott insulator can be ignored, as implied by the BR theory. Physically, this may be well justified for triangular lattices, where both the geometric frustration and the importance of ring exchange processes¹⁰ conspire to render the spin correlations negligibly weak in the experimentally relevant energy (temperature) range.

To implement the BR approach for our problem, we follow the standard methods,¹¹ where (for simplicity) we have taken $U \rightarrow \infty$. The free energy (per electron) of the self-doped system then takes the form

$$W[\lambda, Z, \mu, \delta] = - \frac{2T}{1 - \delta} \sum_{lk} \ln\{1 + \exp[-(E_{lk} - \mu)/T]\} + \frac{\lambda}{1 - \delta} (Z - 1) + \mu, \quad (2)$$

where T is temperature, E_{lk} are renormalized band energies, λ is the Lagrange multiplier imposing the occupancy constraint, Z is the quasiparticle weight, and μ is the chemical potential. The free energy $W[\lambda, Z, \mu, \delta]$ is stationary in the ground state: $\partial W / \partial a = 0$, where $a = \lambda, Z, \mu, \delta$.

The two bands of the model are coupled via the hybridization $\sqrt{Z}V$. We further assume that the interstitial band density of states is approximated by a regular function $\nu(\epsilon)$. The renormalized band energies then explicitly read

$$E_{1,2}(\epsilon) = \frac{1}{2}(\varepsilon_f + \varepsilon_c + \epsilon + \lambda) \mp \frac{1}{2}\sqrt{(\varepsilon_c - \varepsilon_f + \epsilon - \lambda)^2 + 4ZV^2}. \quad (3)$$

The hybridization V and the density of states $\nu(\epsilon)$ have explicit dependence on the lattice spacing and hence on the doping δ . The density depends on δ as $\nu(\epsilon, \delta) = \nu[\epsilon/\gamma(\delta)]/\gamma(\delta)$, where $\gamma(\delta=0)=1$. The details of the dependence of V and γ on δ are not of qualitative importance near the transition, as long as $V(\delta)$ and $\gamma(\delta)$ are smooth functions of δ . Note that the van Hove singularities of a triangular lattice are sufficiently far from the Fermi energy at half filling.

The choice of ε_f and ε_c , on the contrary, proves very important. We use effective electrostatic energy parameters to model complex energetics of the problem, arising from strong renormalization of bare parameters by elastic modes. For simplicity, we assume a linear dependence of local po-

tentials on the charge densities of the site and interstitial sublattices:

$$\varepsilon_i = \frac{v_{ij}}{\sqrt{1-\delta}} n_j, \quad (4)$$

where $\{i,j\}=\{f,c\}$, $n_f=1-Z$ and $n_c=Z-\delta$, so the effective potentials depend on both δ and Z . The prefactor $1/\sqrt{1-\delta}$ represents overall rescaling of the Coulomb interaction with the change of the lattice spacing, due to charge neutrality. The coefficient v_{ij} is an effective potential created on an (empty) site of the band i by the fully charged band j . We expect the polarization to play a crucial role in the potential renormalization. When a hole is created, the nearby electrons are attracted to the vacancy, partially screening it. When an electron is placed in the interstitial orbital, the nearby electrons are repelled,⁶ again partially screening the charge fluctuation. The effect of the screening is always directed toward decreasing the energy of the corresponding particle-hole excitation. Due to the elastic softness of the Wigner lattice (e.g., shear phonons with the energy two orders of magnitude smaller, than the bare Coulomb energy), we expect a strong renormalization of the excitation energy, leading to an appreciable reduction in the charge-transfer gap $\varepsilon_c - \varepsilon_f$. Therefore, we assume that $(v_{ff} - v_{cf})/v_{ff} = \alpha \ll 1$. The value of v_{cc} enters only the second order corrections in δ , so we ignore it and simply set to zero. The stability requirement for the classical Wigner crystal restricts the value of v_{fc} . The electrostatic energy of the WC is $E = [\varepsilon_f(1-Z) + \varepsilon_c(Z-\delta)]/(1-\delta)$. In the classical limit, $Z = \delta$ for $\delta > 0$ and $Z = 0$ for $\delta < 0$. By setting $v_{cf} = (1-\alpha)v_{ff}$, we find that the WC is stable only for $v_{fc} > v_{ff}(1/2 + \alpha)$.

SOLUTION OF THE MODEL

The problem can be simplified in the critical regime (when $Z \rightarrow 0$ and $\delta \rightarrow 0$) and analyzed analytically. This allows us to make certain general statement about the nature of the MIT. Away from the transition, we resort to a numerical solution.

Linear analysis and stabilization of the metallic phase via self-doping

In the following, we show that the self-doping (SD) transition always precipitates the transition taking place at half-filling (HF). We obtain a criterion for determining whether the SD is electron, or holelike.

We expand our equations around the insulating solution ($Z=0$, $\delta=0$) to linear order in variations of the parameters λ , Z , μ , δ , assuming $T=0$. At the transition point, $\mu = \varepsilon_f + \lambda$ and the free energy is purely classical: $W_c = \varepsilon_f$. From the saddle point equation $\partial W / \partial \delta = 0$ we find that in the SD transition $W - \mu = -\partial \varepsilon_f / \partial \delta$, hence $\lambda_c = \partial \varepsilon_f / \partial \delta$.

The results of the expansion in small Z can be conveniently summarized in terms of the auxiliary functions $\phi_1(V, \lambda)$ and $\phi_2(V, \lambda)$ defined as

$$\phi_1(V, \lambda) = \lambda + \frac{\partial \varepsilon_f}{\partial Z} - 2V^2 \int_{-\infty}^{E_F} d\varepsilon \nu(\varepsilon) \frac{1}{\varepsilon_c - \varepsilon_f + \varepsilon - \lambda}, \quad (5)$$

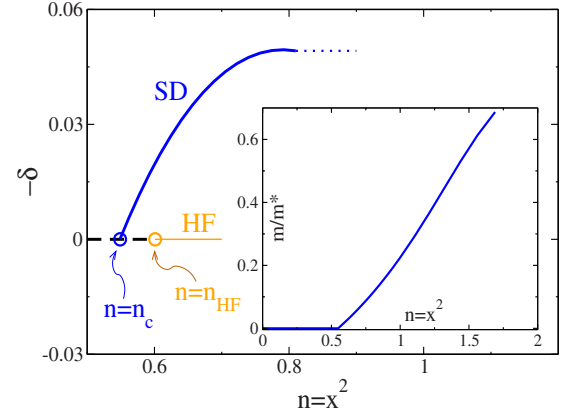


FIG. 1. (Color online) The phase diagram in the zero magnetic field. The MIT takes route via self-doping (thick solid line), which always precipitates the transition at half-filling (thin solid line). The inset shows the quasiparticle weight, vanishing at n_c .

$$\phi_2(V, \lambda) = 1 - 2V^2 \int_{-\infty}^{E_F} d\varepsilon \nu(\varepsilon) \frac{1}{(\varepsilon_c - \varepsilon_f + \varepsilon - \lambda)^2}, \quad (6)$$

where E_F is the Fermi energy. One can check that the equation $\partial W / \partial Z = 0$ for $Z \rightarrow 0$ (at SD or HF transition) is simply $\phi_1(V, \lambda) = 0$. Differentiating this equation [where $V = V(\lambda)$ satisfies the equation] with respect to λ , we have

$$0 = \frac{d\phi_1}{d\lambda} = \phi_2 - 2 \frac{\lambda + \frac{\partial \varepsilon_f}{\partial Z}}{V} \frac{dV}{d\lambda}. \quad (7)$$

It follows from the saddle point equations $\partial W / \partial \lambda = 0$ and $\partial W / \partial \mu = 0$ that at the HF transition $\phi_2(V, \lambda) = 0$. Therefore, according to the Eq. (7), $dV/d\lambda = 0$ at the HF transition. Direct inspection indicates that W has a maximum there, thus the SD transition always occurs before the HF transition.

By considering $\partial W / \partial \lambda = \partial W / \partial \mu = 0$ near the SD transition, one finds that $Z = \delta / \phi_2(V, \lambda_c)$. Therefore, if ϕ_2 is positive in the SD transition, then the doping is holelike, and if ϕ_2 is negative the doping is electronlike. If $\phi_2 = 0$, the SD transition coincides with the MIT transition restricted to half filling.

Numerical solution

We choose the parameters of the model that can best mimic the experimental results. For that, we set $v_{ff} = E_C$, $v_{cf} = (1-\alpha)E_C$, $v_{fc} = 0.1E_C$, where $\alpha = 0.1$ and E_C is the bare Coulomb energy. We use a parameter $x = D_c / |E_C|$ to mimic the r_s number, where D_c is the width of the interstitial band. The electron density goes as $n \sim x^2$ in a 2D electron gas. We set $V = D_c$. The density of states in the interstitial band is constant, mimicking a two dimensional dispersion. For these choice of the parameters, we find [Eqs. (5) and (6)] that the SD transition occurs at $x_{SD} = 0.7408$ ($n_{SD} = 0.549$) and the HF transition occurs at $x_{HF} = 0.7751$ ($n_{SD} = 0.601$).

In contrast to standard Mott transition, the half-filled insulator (heavy dashed line in Fig. 1) thus becomes unstable

to electronlike self-doping (heavy full line in Fig. 1), before the half filled transition takes place (thin full line in Fig. 1). The quasiparticle weight $Z \sim 1/m^* \sim (n - n_c)$ vanishes linearly (see inset of Fig. 1) as the transition is approached from the metallic side, in agreement with experiments.¹

TRANSPORT, EFFECT OF MAGNETIC FIELD, AND PHASE DIAGRAM

Different properties have been studied in detail for various Mott systems using recently developed DMFT method¹²—a reliable tool even at low dimensions (unless the critical properties are specifically tied to the system’s dimensionality). This approach can be regarded as a finite temperature generalization of the BR theory we utilized. Armed with this knowledge, one can directly list what is expected within the framework we consider: (1) Below the transition, transport takes place by activation $\rho(T) \sim \exp[-\Delta_o(n)/T]$, with $\Delta_o(n) \propto n_c - n$, just as seen in the experiments.¹ (2) On the metallic side, heavy quasiparticles exist only below a coherence temperature $T^*(n) \sim 1/m^* \sim (n - n_c)$, leading¹³ to a large resistivity drop¹ at $T < T^*(n)$. (3) A parallel magnetic field $B_{\parallel}^*(n) \sim 1/m^* \sim (n - n_c)$ is sufficient to produce full spin polarization of the electrons, destroying the coherent quasiparticles and causing large and positive magnetoresistance.¹ (4) Close to the transition, at $B_{\parallel} > B_{\parallel}^*(n)$, the resistivity saturates to a field-independent value $\rho(T) \rightarrow \rho_{\infty}(T)$, which assumes an activated form $\rho_{\infty}(T) \sim \exp(-\Delta_{\infty}(n)/T)$, where the gap $\Delta_{\infty}(n)$ remains finite in the high field limit. This behavior is specific to a charge-transfer (CT) model we consider, since the charge-transfer gap Δ_{CT} remains finite as $B_{\parallel} \rightarrow \infty$, in contrast to the standard Mott gap $\Delta_{Mott} = U + g\mu_B B_{\parallel}$. (5) In the CT model, the MIT reduces to a band-crossing transition in the $B_{\parallel} \rightarrow \infty$ limit, where $\Delta_{\infty}(n) \sim (n_c^{\infty} - n)$ vanishes at $n_c^{\infty} > n_c$, and the system remains metallic at higher densities. (6) The resulting phase diagram (Fig. 2) agrees well with the experimental one¹⁴ obtained for ultraclean samples.

CONCLUSIONS

We presented a theory for the interaction-driven MIT describing the clean 2DEG. Our approach focuses on vacancy-interstitial excitations within a Wigner-Mott insulator, naturally leading to a two-band (charge-transfer) Hubbard model. As density increases, such excitations lead to an instability of the insulating state, and produce a self-doping driven Mott transition to a heavy electron metal. The general predictions of this model seem to explain most puzzling features seen in

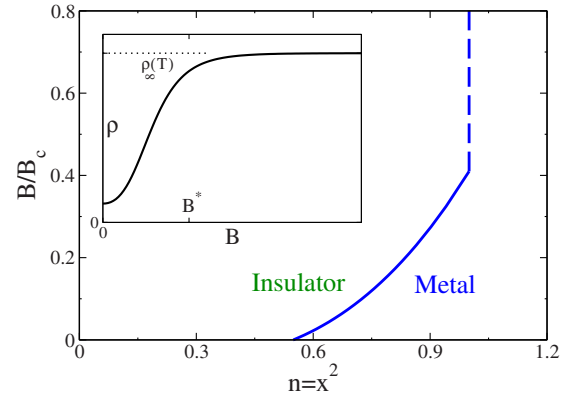


FIG. 2. (Color online) The metal-insulator phase diagram in the presence of a parallel magnetic field (in units of $B_c = n_c / \mu_B g m$). The dashed line represents a metal to band insulator transition. The electron spin becomes fully polarized at the magnetic field B^* . The inset shows the change in resistivity from Fermi liquid to insulating behavior as the magnetic field exceeds B^* .

the experiment, strongly suggesting that Coulomb interactions and not disorder provide the fundamental driving force for the 2D-MIT.

The most challenging task for future work is to extend the present approaches to explicitly include the dynamics of collective charge fluctuations which are phenomenologically treated in the considered lattice model. This goal should be facilitated by recent advances¹⁵ in theories for Coulomb gap phenomena, and would provide a more rigorous justification of the lattice model we introduced. Even more importantly, such a theory will be indispensable to understand experiments¹⁶ at temperatures and densities where the Wigner lattice has already melted, but where strong short-range charge correlations persist. Such a regime is of appreciable importance and extent whenever the reduced Coulomb interaction strength $r_s \gg 1$, as found in many experiments on the 2DEG.

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¹For a review, see S. V. Kravchenko and M. P. Sarachik, Rep. Prog. Phys. **67**, 1 (2004), and references therein.

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